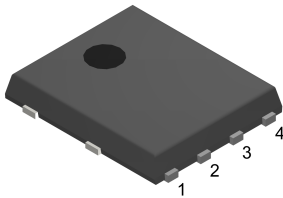
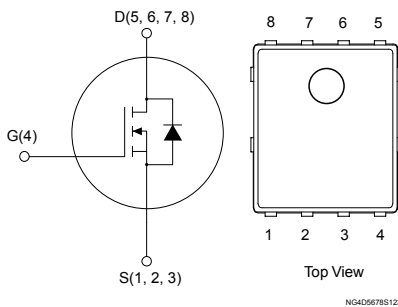


N-channel 80 V, 5.2 mΩ typ., 100 A, STripFET F7 Power MOSFET in a PowerFLAT 5x6 package


PowerFLAT 5x6


Features

Order code	V_{DS}	$R_{DS(on) \max}$	I_D	P_{TOT}
STL100N8F7	80 V	6.1 mΩ	100 A	120 W

- Among the lowest $R_{DS(on)}$ on the market
- Excellent FoM (figure of merit)
- Low C_{rSS}/C_{iSS} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.



Product status link

[STL100N8F7](#)

Product summary

Order code	STL100N8F7
Marking	100N8F7
Package	PowerFLAT 5x6
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	80	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	100	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	71	A
$I_{DM}^{(2)(1)}$	Drain current (pulsed)	400	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	20	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	14	A
$I_{DM}^{(3)(2)}$	Drain current (pulsed)	80	A
$P_{TOT}^{(1)}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	120	W
$P_{TOT}^{(3)}$	Total power dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4.8	W
$E_{AS}^{(4)}$	Single pulse avalanche energy	220	mJ
T_J	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature range		$^\circ\text{C}$

1. This value is rated according to R_{thj-c} .
2. Pulse width limited by safe operating area.
3. This value is rated according to $R_{thj-pcb}$.
4. Starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = 25\text{ A}$, $V_{DD} = 40\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.25	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	$^\circ\text{C/W}$

1. When mounted on FR-4 board of 1 inch^2 , 2oz Cu, $t < 10\text{ s}$.

2 Electrical characteristics

($T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Table 3. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	80			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 80\text{ V}$			1	μA
		$V_{GS} = 0, V_{DS} = 80\text{ V},$ $T_C = 125\text{ }^\circ\text{C}$ (1)			10	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		5.2	6.1	m Ω

1. Defined by design, not subject to production test.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$	-	3435	-	pF
C_{oss}	Output capacitance		-	653	-	pF
C_{riss}	Reverse transfer capacitance		-	57	-	pF
Q_g	Total gate charge	$V_{DD} = 40\text{ V}, I_D = 20\text{ A},$	-	46.8	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	23.4	-	nC
Q_{gd}	Gate-drain charge	(see Figure 13. Test circuit for gate charge behavior)	-	11.2	-	nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 40\text{ V}, I_D = 10\text{ A}, R_G = 4.7\text{ }\Omega,$ $V_{GS} = 10\text{ V}$	-	49	-	ns
t_r	Rise time		-	95	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	60	-	ns
t_f	Fall time		-	32	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$V_{GS} = 0, I_{SD} = 20 \text{ A}$	-		1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 20 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s},$	-	48.6		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60 \text{ V}$ (see Figure 14. Test circuit for inductive load switching and diode recovery times.	-	58.6		nC
I_{RRM}	Reverse recovery current		-	2.4		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

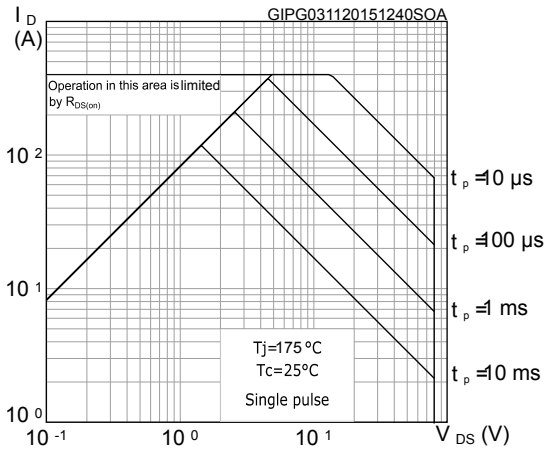


Figure 2. Thermal impedance

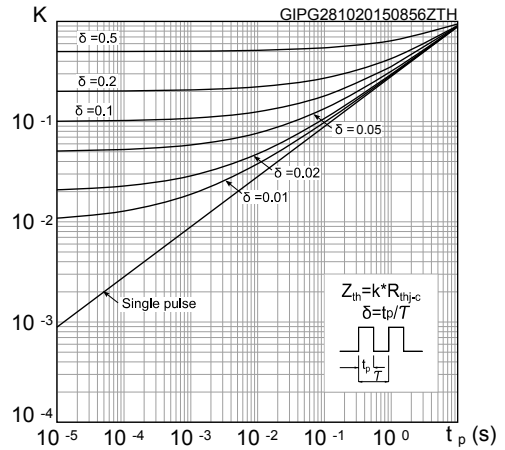


Figure 3. Output characteristics

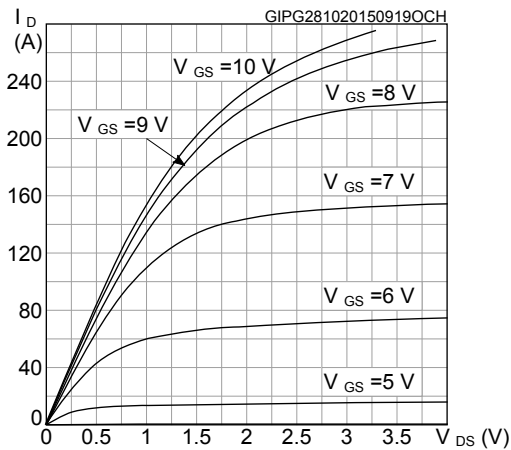


Figure 4. Transfer characteristics

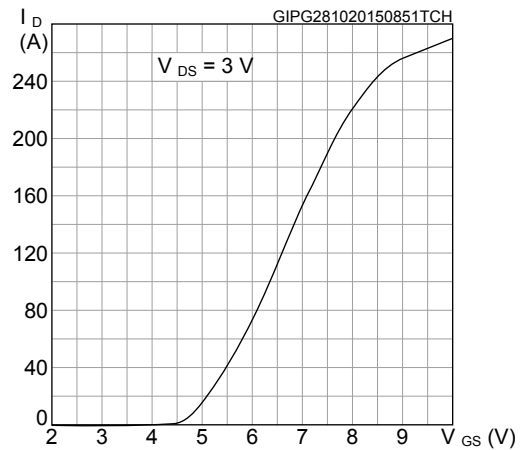


Figure 5. Gate charge vs gate-source voltage

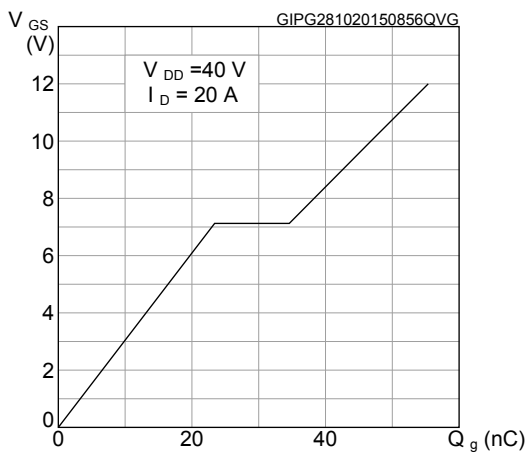


Figure 6. Static drain-source on-resistance

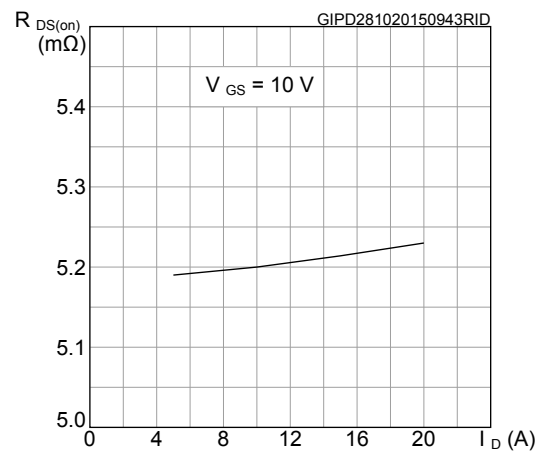


Figure 7. Capacitance variations

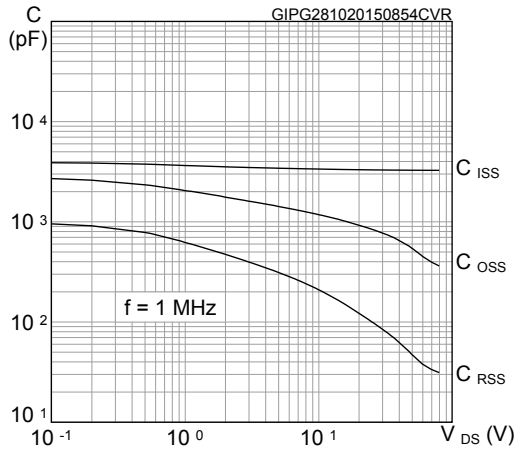


Figure 8. Normalized gate threshold voltage vs temperature

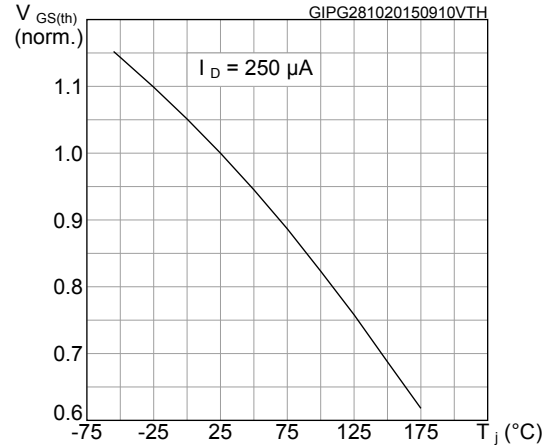


Figure 9. Normalized on-resistance vs temperature

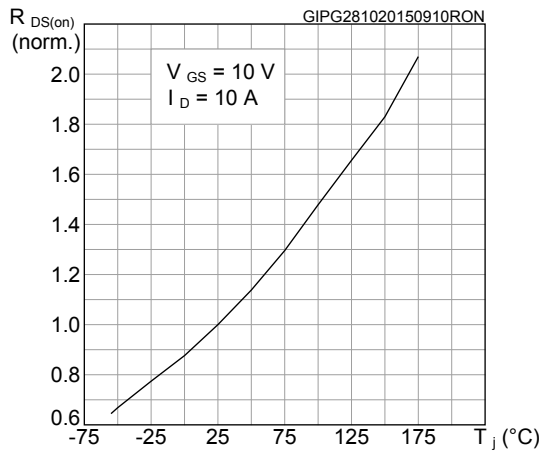


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

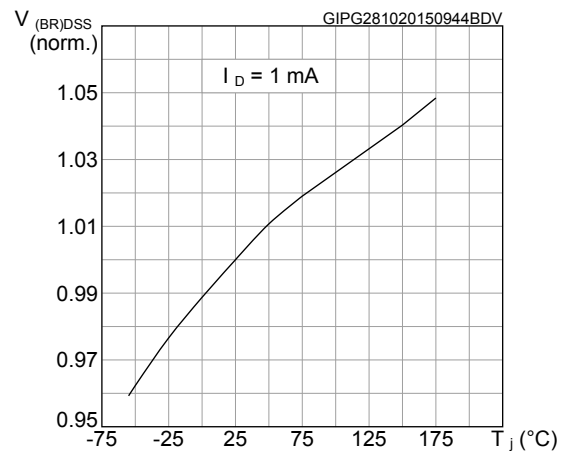
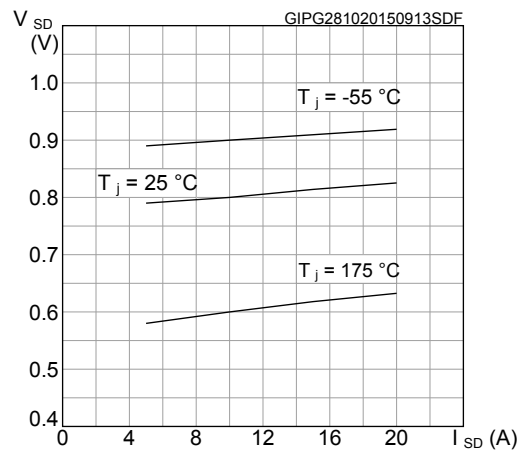
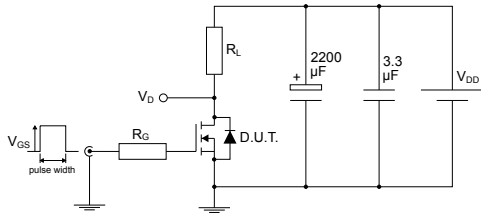


Figure 11. Source-drain diode forward characteristics



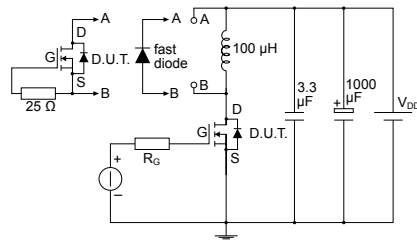
3 Test circuits

Figure 12. Test circuit for resistive load switching times


AM01468v1

Figure 13. Test circuit for gate charge behavior


AM01469v1

Figure 14. Test circuit for inductive load switching and diode recovery times


AM01470v1

Figure 15. Unclamped inductive load test circuit


AM01471v1

Figure 16. Unclamped inductive waveform


AM01472v1

Figure 17. Switching time waveform

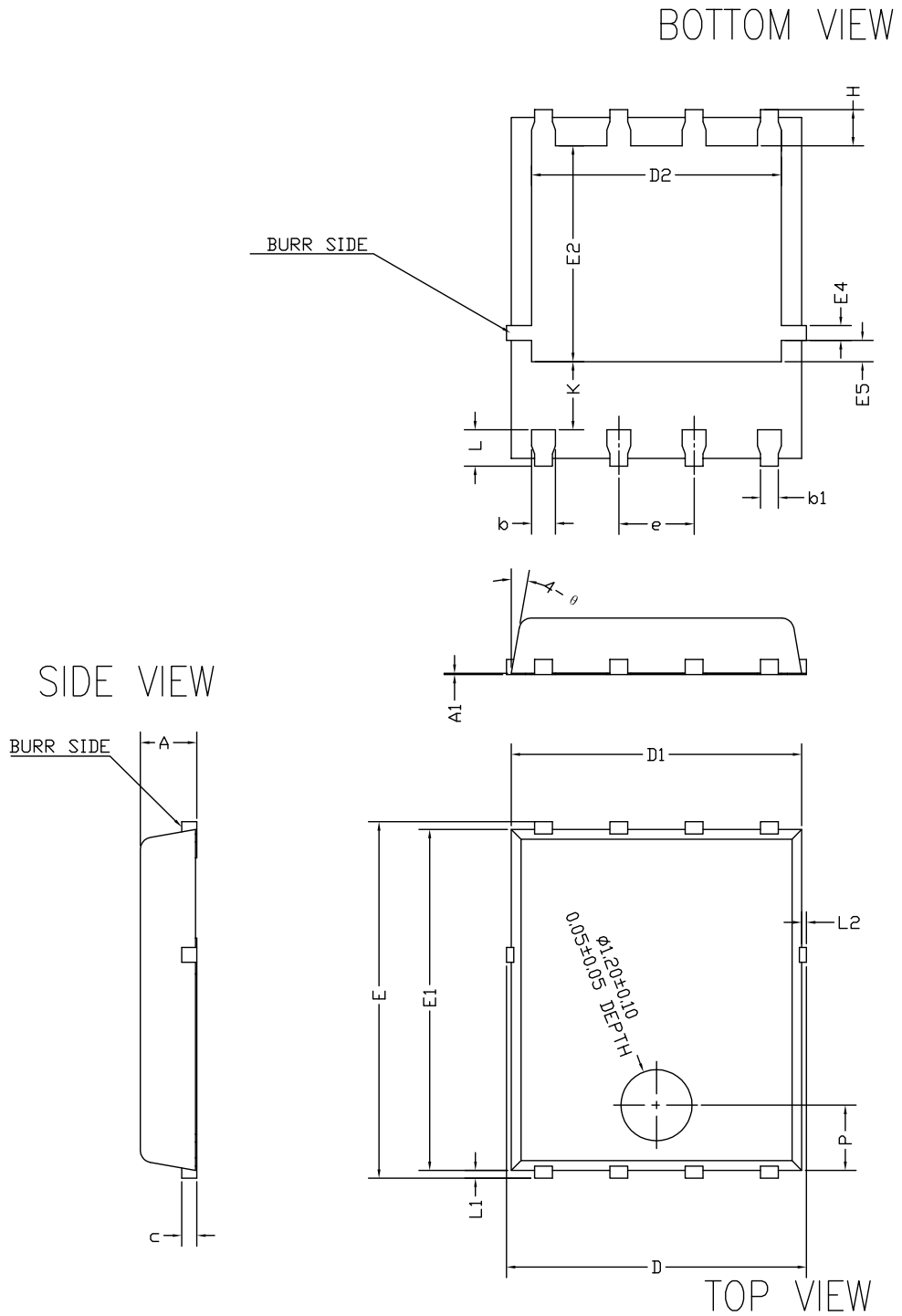

AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 PowerFLAT 5x6 type C SUBCON package information

Figure 18. PowerFLAT 5x6 type C SUBCON package outline



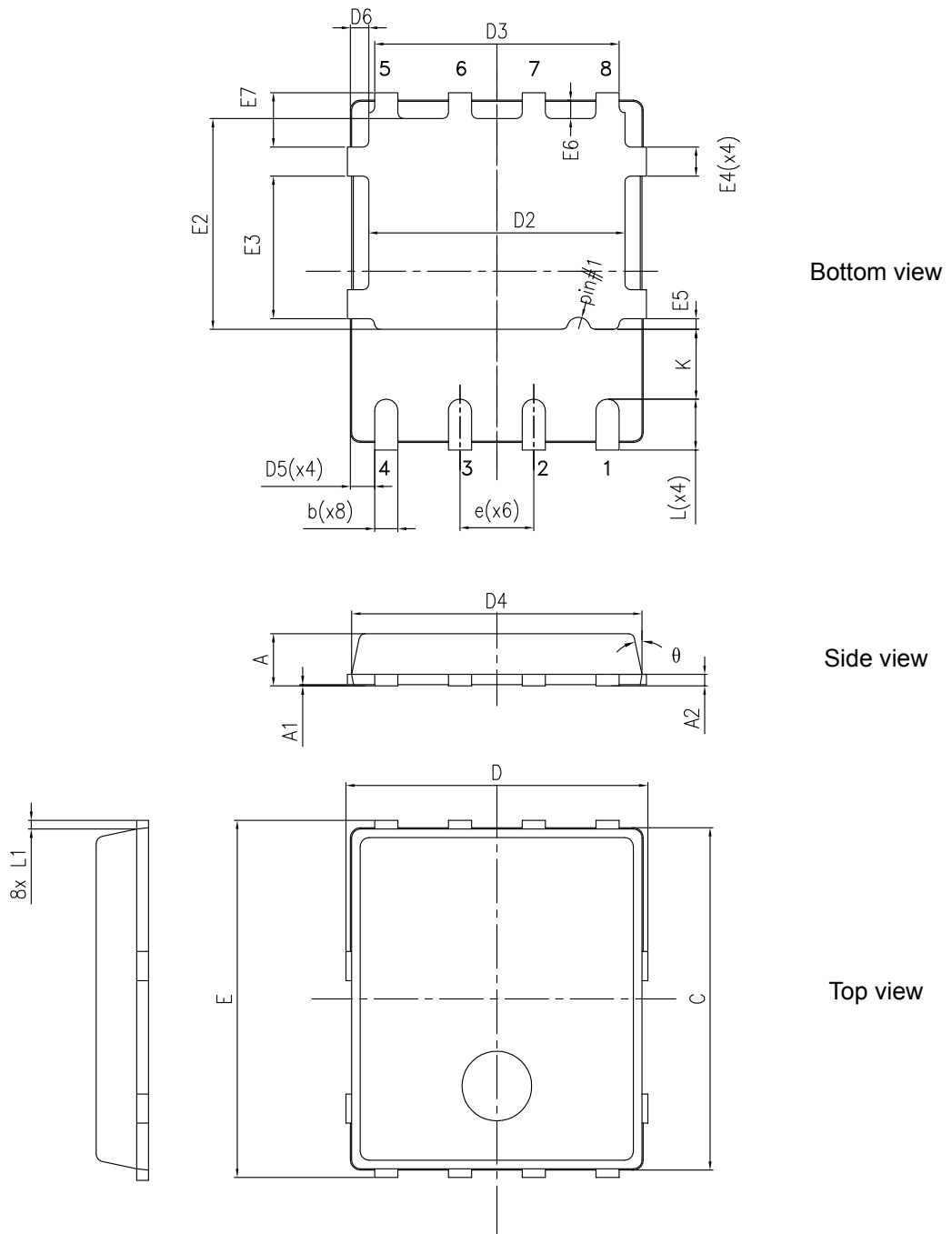
8472137_SUBCON_998G_REV4

Table 7. PowerFLAT 5x6 type C SUBCON package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.90	0.95	1.00
A1		0.02	
b	0.35	0.40	0.45
b1		0.30	
c	0.21	0.25	0.34
D			5.10
D1	4.80	4.90	5.00
D2	4.01	4.21	4.31
e	1.17	1.27	1.37
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.54	3.64	3.74
E4	0.15	0.25	0.35
E5	0.26	0.36	0.46
H	0.51	0.61	0.71
K	0.95		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
L2			0.10
P	1.00	1.10	1.20
θ	8°	10°	12°

4.2 PowerFLAT 5x6 type C package information

Figure 19. PowerFLAT 5x6 type C package outline

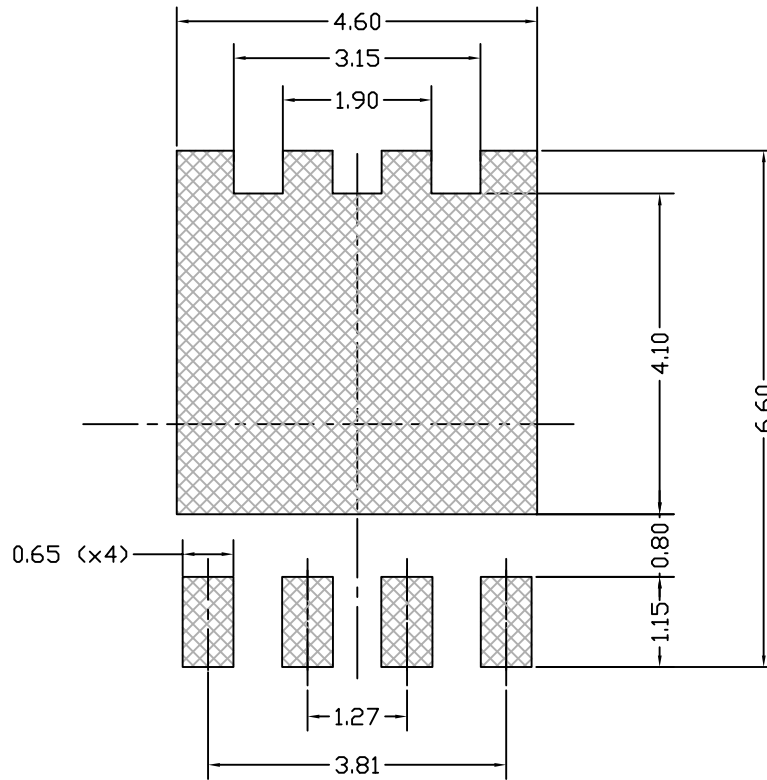


8231817_typeC_Rev18

Table 8. PowerFLAT 5x6 type C package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.20
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.20
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
e		1.27	
E	5.95	6.15	6.35
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.75	0.90	1.05
K	1.05		1.35
L	0.725		1.025
L1	0.05	0.15	0.25
θ	0°		12°

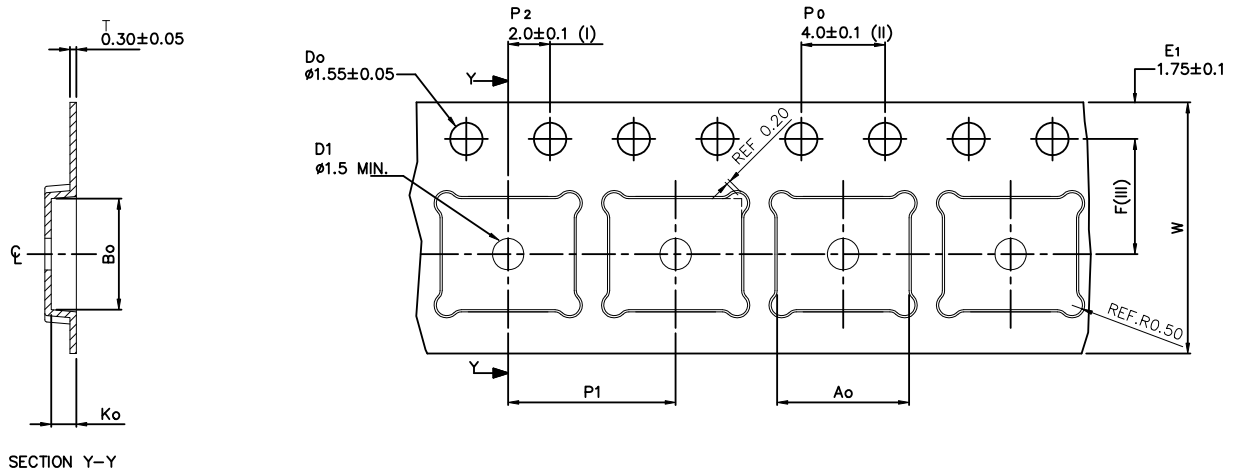
Figure 20. PowerFLAT 5x6 recommended footprint (dimensions are in mm)



8231817_FOOTPRINT_simp_Rev_18

4.3 PowerFLAT 5x6 packing information

Figure 21. PowerFLAT 5x6 tape (dimensions are in mm)



A ₀	6.30 +/- 0.1
B ₀	5.30 +/- 0.1
K ₀	1.20 +/- 0.1
F	5.50 +/- 0.1
P ₁	8.00 +/- 0.1
W	12.00 +/- 0.3

(I) Measured from centreline of sprocket hole to centreline of pocket.

(II) Cumulative tolerance of 10 sprocket holes is ± 0.20 .

(III) Measured from centreline of sprocket hole to centreline of pocket

Base and bulk quantity 3000 pcs
All dimensions are in millimeters

8234350_Tape_rev_C

Figure 22. PowerFLAT 5x6 package orientation in carrier tape

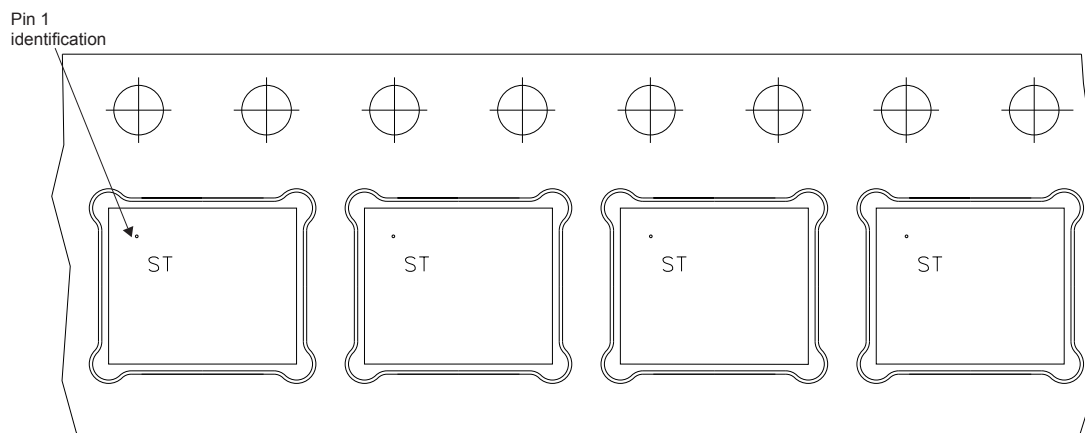
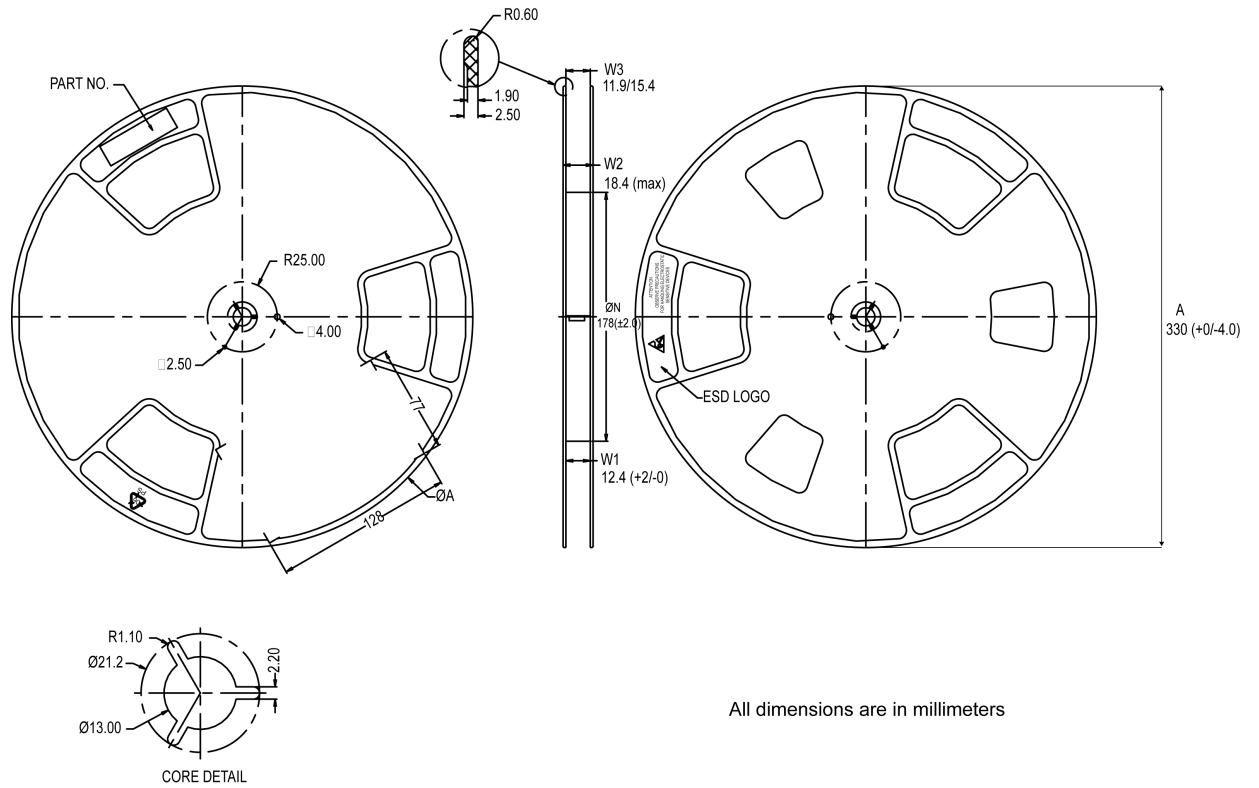


Figure 23. PowerFLAT 5x6 reel



All dimensions are in millimeters

8234350_Reel_rev_C

Revision history

Table 9. Document revision history

Date	Revision	Changes
21-Oct-2014	1	Initial release.
03-Nov-2015	2	Modified: Table 2: "Absolute maximum ratings" , Table 5: "Dynamic", Table 6: "Switching times" and Table 7: "Source drain diode". Added: Section 4.1: "Electrical characteristics (curves)". Minor text changes
03-Dec-2015	3	Document status promoted from preliminary to production data.
27-Nov-2019	4	Added Section 4.1 PowerFLAT 5x6 type C SUBCON package information . Updated Section 4.2 PowerFLAT 5x6 type C package information . Minor text changes.

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4.2	PowerFLAT 5x6 type C package information	10
4.3	PowerFLAT™ 5x6 type C packing information	13
	Revision history	16

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